

N-Channel 40 V (D-S) MOSFET



COMPLIANT

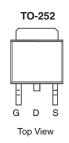
PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}$ (m Ω)(Typ.)	I _D (A) ^a (Max.)			
40	1.7 at V _{GS} = 10 V	180			
40	2.4 at V _{GS} = 4.5 V	120			

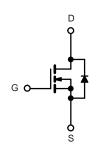
FEATURES

- 175 °C Junction Temperature
- DT-Trench Power MOSFET

APPLICATIONS

- DC Motor Driver
- Synchronous Rectification in DC/DC and AC/DC Converters





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
Parameter		Symbol	Limit	Unit		
Gate-Source Voltage		V _{GS}	± 20	V		
Continuous Drain Current (T _{.I} = 175 °C) ^b	T _C = 25 °C	1_	180			
Continuous Drain Current (1 _J = 175 °C) ²	T _C = 100 °C	l I _D	105 ^a			
Pulsed Drain Current	I _{DM}	720	А			
Continuous Source Current (Diode Conduction)	I _S	180				
Avalanche Current		I _{AS}	178			
Single Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E _{AS}	405 ^c	mJ		
Maximum Power Dissipation	T _C = 25 °C	P _D	206	W		
Maximum Fower Dissipation	T _A = 25 °C	'D	3.5 ^b , 8.8 ^{b, c}			
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Manianum lumation to Ambianta	t ≤ 10 sec	R _{thJA}	13	18	°C/W	
Maximum Junction-to-Ambient ^a	Steady State		35	50		
Maximum Junction-to-Case		R _{thJC}	0.6	1.0		

Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- $c.\ t \leq 10\ s.$

Rev. 1. 0



Parameter	Symbol	Test Conditions	Test Conditions Min.		Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	40			V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1		3	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$) V, V _{GS} = ± 20 V		± 100	nA
		V _{DS} = 40 V, V _{GS} = 0 V			1	μA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 32 V, V _{GS} = 0 V, T _J = 125 °C			50	
		$V_{DS} = 32 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 175 \text{ °C}$			250	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	180			Α
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A		1.7	2.5	mΩ
		$V_{GS} = 4.5 \text{ V}, I_D = 20 \text{ A}$		2.4	3.8	11122
Forward Transconductance ^b	9 _{fs}	$V_{DS} = 5 \text{ V}, I_{D} = 20 \text{ A}$		110		S
Dynamic	•		•	•		
Input Capacitance	C _{iss}			2750		pF
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		493		
Reverse Transfer Capacitance	C _{rss}			65		
Total Gate Charge ^c	Qg			67	90	
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 20 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 20 \text{ A}$		20		nC
Gate-Drain Charge ^c	Q_{gd}			15.5		
Turn-On Delay Time ^c	t _{d(on)}			11		
Rise Time ^c	t _r	V_{DD} = 20 V, R_L = 0.6 Ω		16		ns
Turn-Off Delay Time ^c	t _{d(off)}	$I_D = 20 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$		35		115
Fall Time ^c	t _f			20		
Source-Drain Diode Ratings and Cha	aracteristics (T _C = 25 °C)				
Pulsed Current	I _{SM}				280	А
Diode Forward Voltage	V _{SD}	$I_F = 1 A, V_{GS} = 0 V$		1	1.5	V
Reverse Recovery Time	t _{rr}	$I_F = 20 \text{ A}, \text{ di/dt} = 500 \text{ A/}\mu\text{s}$		45	100	ns
Reverse Recovery Charge	Q _{rr}	$I_F = 20 \text{ A}, \text{ di/dt} = 500 \text{ A/}\mu\text{s}$		45	100	ns

Notes:

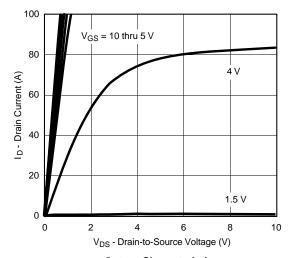
- a. For design aid only; not subject to production testing. b. Pulse test; pulse width $\,300~\mu s$, duty cycle $\,2~\%.$
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

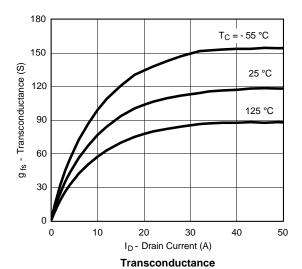




TYPICAL CHARACTERISTICS (25 °C unless noted)

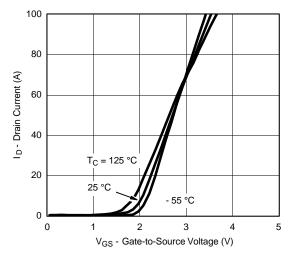


Output Characteristics

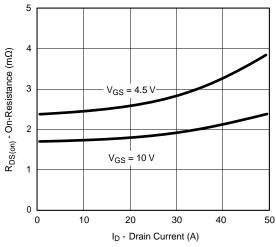


3600 3150 2700 C_{iss} C - Capacitance (pF) 2250 1800 1350 900 $\mathsf{C}_{\mathsf{oss}}$ 450 0 0 10 30 60 V_{DS} - Drain-to-Source Voltage (V)

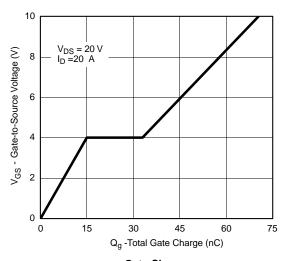
Capacitance



Transfer Characteristics



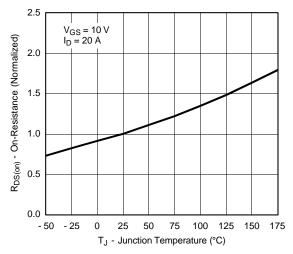
On-Resistance vs. Drain Current



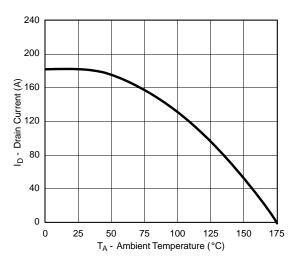
Gate Charge



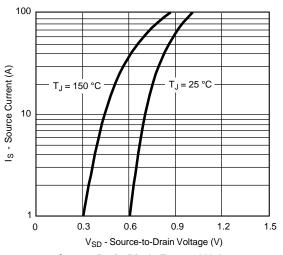
TYPICAL CHARACTERISTICS (25 °C unless noted)



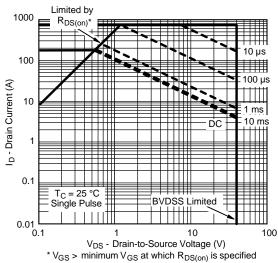
On-Resistance vs. Junction Temperature



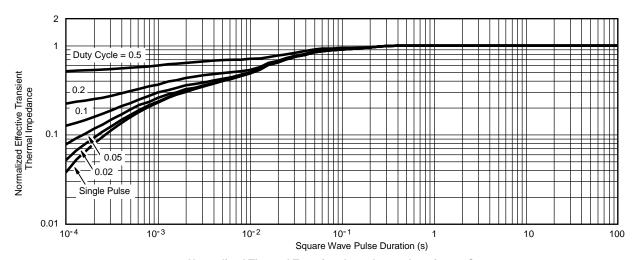
Maximum Drain Current vs. Ambient Temperature



Source-Drain Diode Forward Voltage



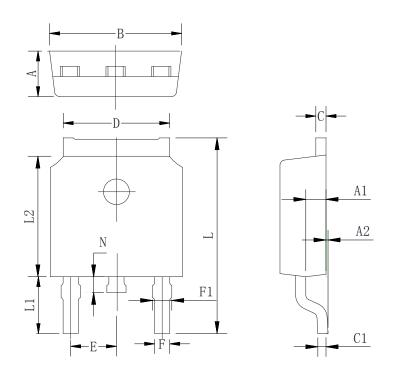
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case



TO-252-2L PACKAGE OUTLINE DIMENSIONS



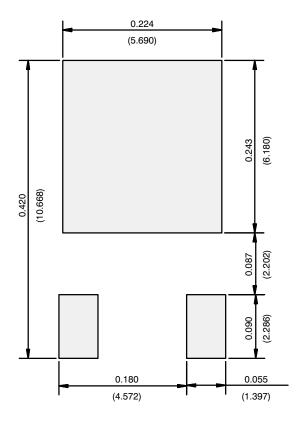
UNIT: mm

Symbol	Min	Тур	Max	
A	2.20	2.30	2.40	
A1	0.91	1.01	1.11	
A2	0.05	0.15	0.25	
В	6.45	6.60	6.75	
С	0.45	0.50	0.58	
C1	0.45	0.50	0.58	
D	5.12	5.32	5.52	
Е	2.286 TYP			
F	0.66	0.76	0.86	
F1	0.66	0.86	1.06	
L	9.60	9.90	10.20	
L1	2.6	2.8	3.0	
L2	5.95	6.10	6.25	
N	0.60	0.80	1.00	



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RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)



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